

FIG. 1

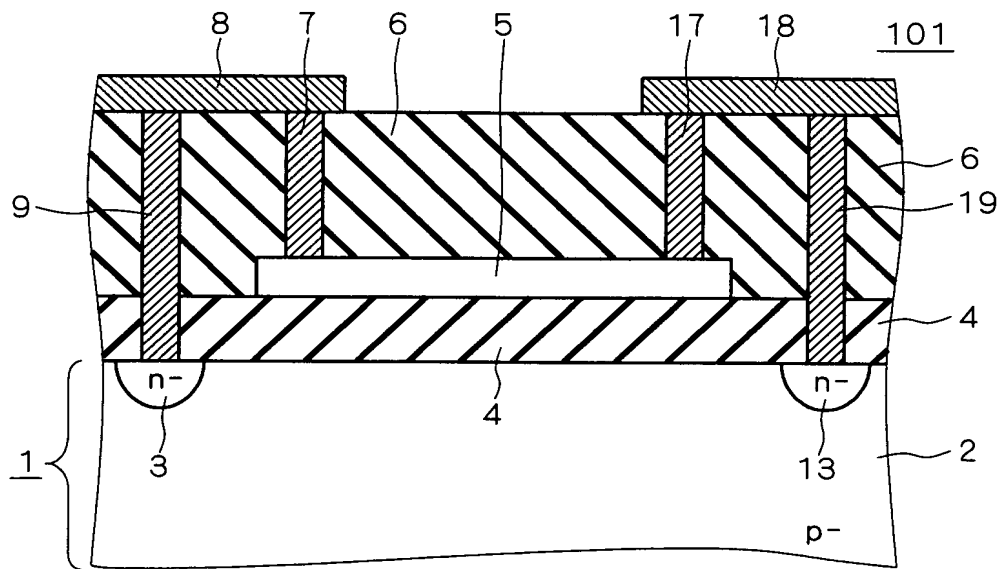


FIG. 2

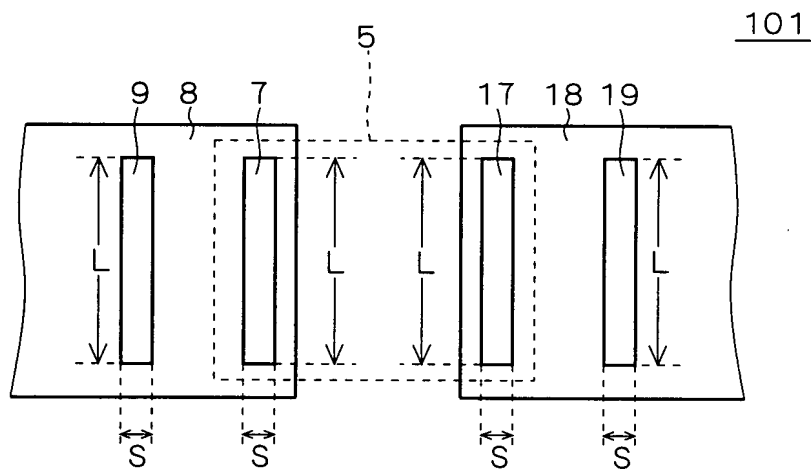
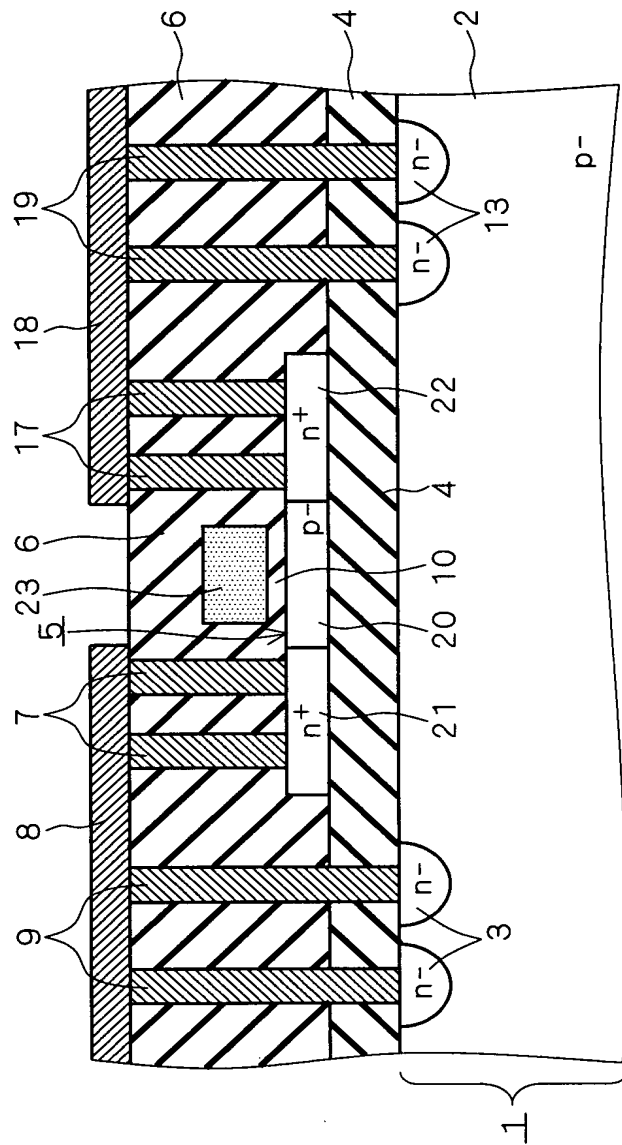
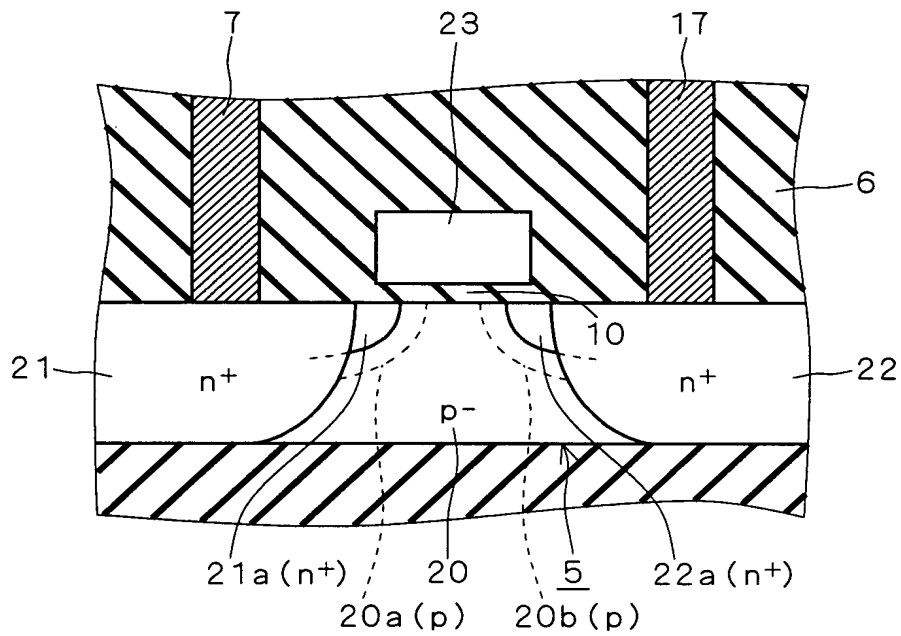


FIG. 3

102



*F / G. 5*



104

18

6

19

4

30

2

p-

1

FIG. 8

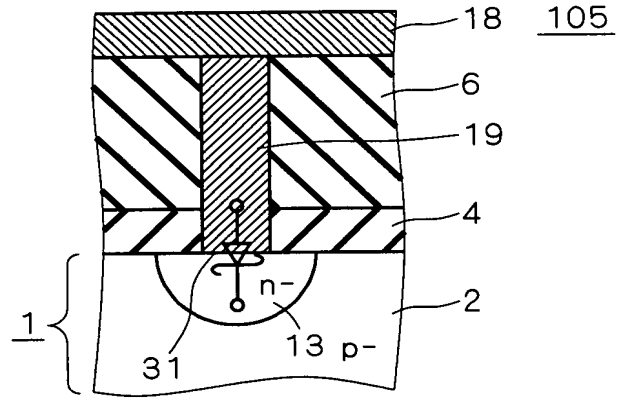
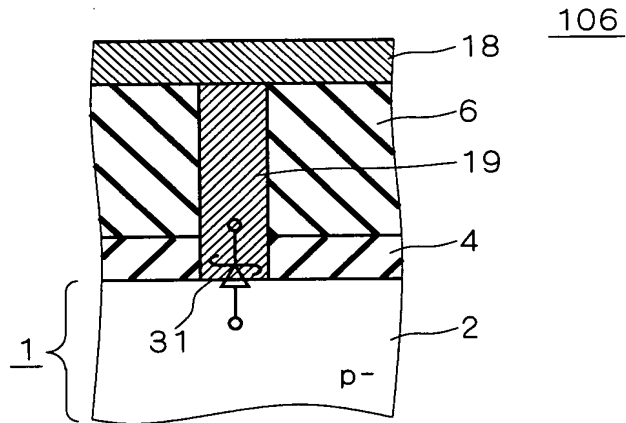


FIG. 9



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[illegible]

*F / G. 13*

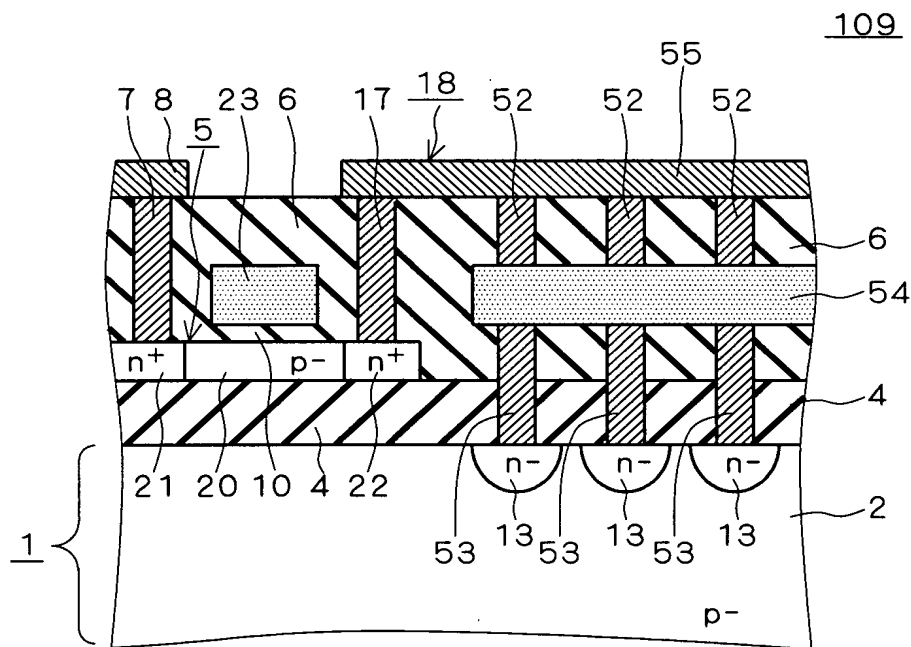


FIG. 14

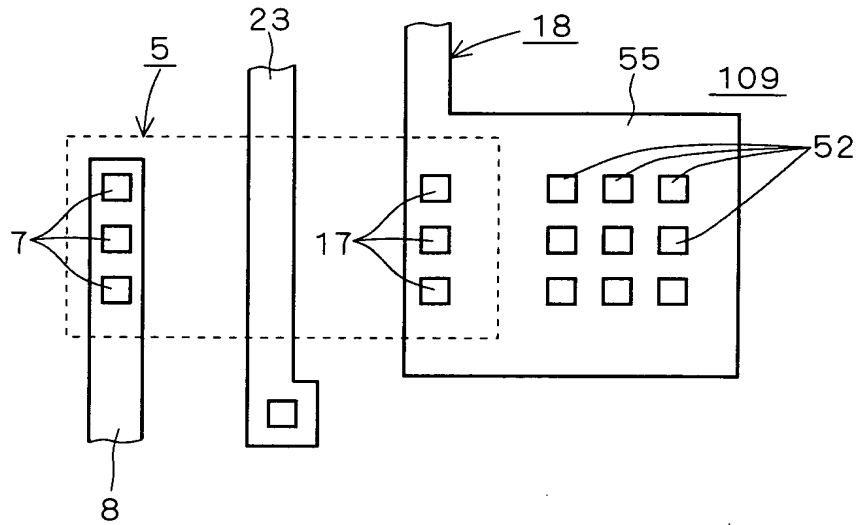
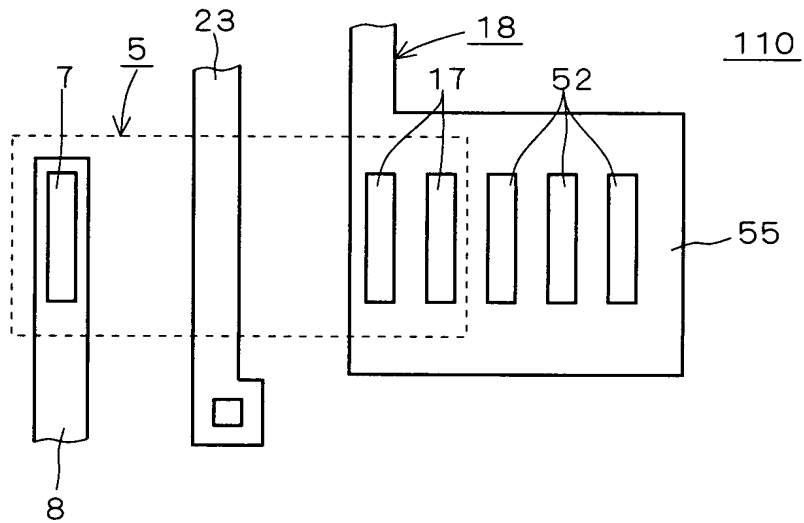


FIG. 15



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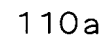
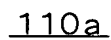




Figure 111 is a cross-sectional view of a semiconductor device. It shows a substrate 6 with a patterned layer 62. Above this is a layer 64 with a patterned layer 66. A central region 70 is defined by a layer 72 and a layer 76. The device is capped by a layer 73 with a patterned layer 74. A bracket 80 groups the upper layers 81, 82, 83, 84, 85, and 86. Two large, semi-circular features 87 and 88 are positioned on top of the device.

FIG. 21 (BACKGROUND ART)

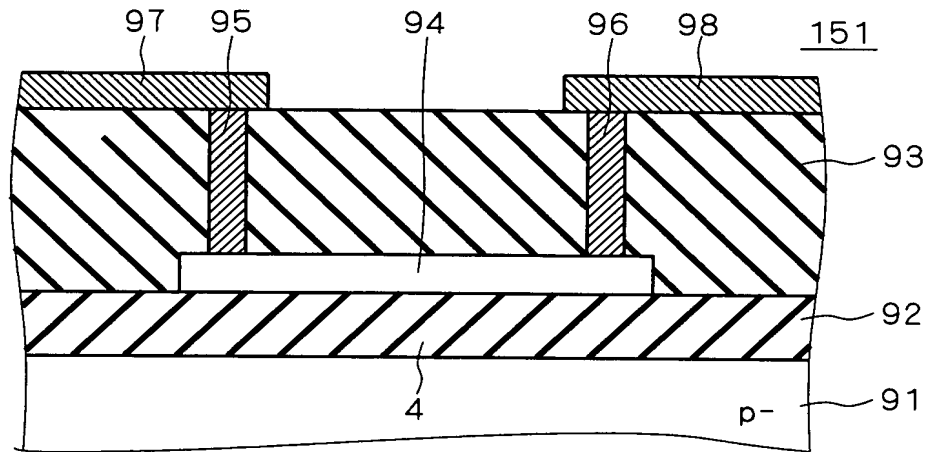


FIG. 22 (BACKGROUND ART)

